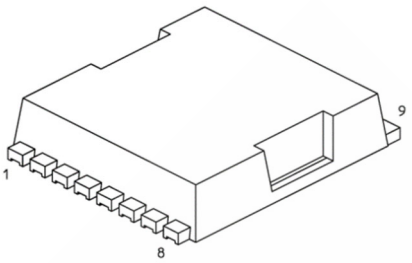
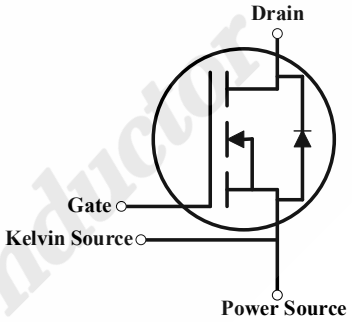
SiC MOS I3M06060L8
N-Channel Enhancement Mode



Features

- High Blocking Voltage with Low On-Resistance
- High-Frequency Operation
- Ultra-Small Q_{gd}
- 100% UIS tested



Benefits

- Improve System Efficiency
- Increase Power Density
- Reduce Heat Sink Requirements
- Reduction of System Cost

TOLL

Gate	1
Kelvin Source	2
Power Source	3~8
Drain	9

Applications

- Solar Inverters
- EV Battery Chargers
- High Voltage DC/DC Converters
- Switch Mode Power Supplies

RoHS

Halogen

Order Information

Part Number	Package	Marking
I3M06060L8	TOLL	I3M06060L8

Contents

1. Maximum Ratings

At T_J= 25℃, unless specified otherwise

Parameter	Symbol	Value	Unit	Test Conditions
Drain - Source Voltage	V_{DSmax}	650	V	V_{GS}= 0V I_D= 100μA
Gate - Source Voltage (dynamic)	V_{GSmax}	-8 / +20	V	AC (f>1 Hz)
Gate - Source Voltage(static) turn-on gate voltage turn-off gate voltage	$V_{GS,on}$ $V_{GS,off}$	+15 / +18 -3	V	Static
Continuous Drain Current	I_D	35	A	V_{GS}= 18V T_C= 25℃
		25		V_{GS}= 18V T_C= 100℃
Power Dissipation	P_D	147	W	
Operating Junction	T_J	-55 To +150	℃	
Storage Temperature	T_{stg}	-55 To +150	℃	
Solder Temperature	T_L	260	℃	

2. Electrical Characteristics

At T_J= 25℃, unless specified otherwise

Parameter	Symbol	Value			Unit	Test Conditions
		Min.	Typ.	Max.		
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	650	/	/	V	V_{GS}= 0V I_D= 100μA
Gate Threshold Voltage	$V_{GS(th)}$	1.8	2.4	/	V	(tested after 30ms pulse at V_{GS}=15V) V_{DS}= V_{GS} I_D= 5mA T_J = 25℃
		/	1.8	/	V	V_{DS}= V_{GS} I_D= 5mA T_J = 150℃
Zero Gate Voltage Drain Current	I_{DSS}	/	1	100	μA	V_{GS}=0V V_{DS}=650V
Gate-Source Leakage Current	I_{GSS}	/	20	250	nA	V_{GS}= 18V V_{DS}= 0V
Drain-Source On-State Resistance	$R_{DS(on)}$	/	60	78	mΩ	V_{GS}= 18V I_D= 20A T_J = 25℃
Trans conductance	g_{fs}	/	12	/	S	V_{DS}= 20V I_{DS}= 20A T_J = 25℃
		/	11	/		V_{DS}= 20V I_{DS}= 20A T_J= 150℃
Input Capacitance	C_{iss}	/	1733	/	pF	V_{GS}= 0V V_{DS}= 400V

Parameter	Symbol	Value			Unit	Test Conditions
		Min.	Typ.	Max.		
Output Capacitance	C_{oss}	/	136.6	/		f= 1MHz V_{AC}= 25mV
Reverse Transfer Capacitance	C_{rss}	/	17.3	/		
Coss Stored Energy	E_{oss}	/	13.6	/	μJ	
Turn-on Energy	E_{on}	/	22.1	/	μJ	V_{DS}=400V V_{GS}=-3/15V I_D=20A R_G=1Ω
Turn-off Energy	E_{off}	/	6.5	/		
Turn-on Energy	E_{on}	/	11.1	/	μJ	V_{DS}=400V V_{GS}=-3/18V I_D=20A R_G=1Ω
Turn-off Energy	E_{off}	/	4.6	/		
Turn-on Delay Time	$T_{d(on)}$	/	12.6	/	ns	
Rise Time	T_r	/	5.6	/		
Turn-off Delay Time	$T_{d(off)}$	/	22.6	/		
Fall Time	T_f	/	5.6	/		
Internal Gate Resistance	$R_{G(int)}$	/	1.1	/	Ω	f= 1MHz V_{AC}= 25mV
Gate to Source Charge	Q_{gs}	/	17.5	/	nC	V_{DS}= 400V I_{DS}= 20A V_{GS}= -3 to 18V I_G= 50mA
Gate to Drain Charge	Q_{gd}	/	15.3	/		

Parameter	Symbol	Value			Unit	Test Conditions
		Min.	Typ.	Max.		
Total Gate Charge	Q_g	/	53.1	/		

3. Reverse Diode Characteristics

At T_J= 25℃, unless specified otherwise

Parameter	Symbol	Value		Unit	Test Conditions
		Typ.	Max.		
Diode Forward Voltage	V_{SD}	5.7	/	V	V_{GS}= -3V I_{SD}= 10A T_J= 25℃
		5.1	/	V	V_{GS}= -3V I_{SD}= 10A T_J= 150℃
Continuous Diode Forward Current	I_S	24	/	A	V_{GS}= -3V
Reverse Recover Time	t_{rr}	12.8	/	ns	V_{GS}=-3V I_{SD}=20A V_R=400V d_{if}/d_t=3200A/ns T_J=25℃
Reverse Recover Charge	Q_{rr}	264.4	/	nC	
Peak Reverse Recovery Current	I_{rrm}	32.8	/	A	

4. Thermal Characteristics

Parameter	Symbol	Value	Unit
Thermal Resistance from Junction to Case	$R_{\theta JC}$	1.02	℃/W

5. Typical Performance

At T_J= 25℃, unless specified otherwise

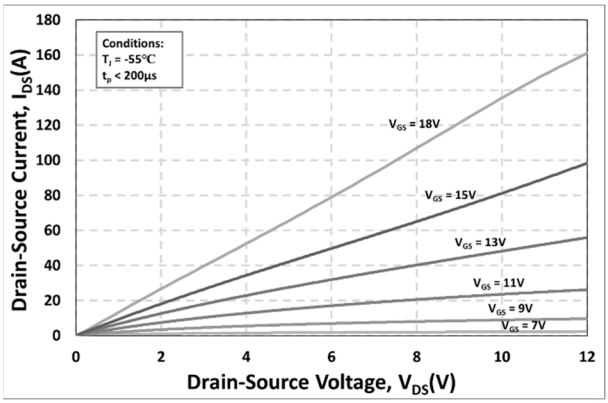


Figure 1. Output Characteristics T_J = -55℃

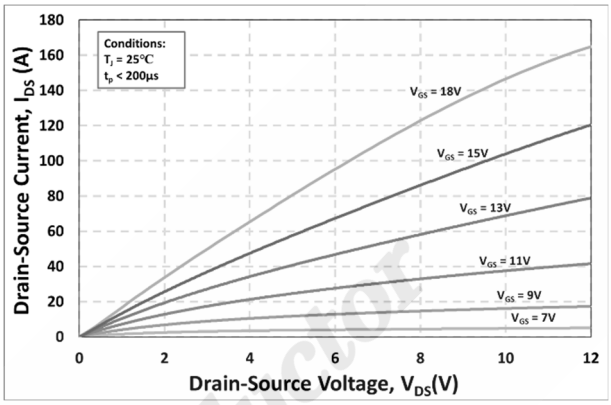


Figure 2. Output Characteristics T_J = 25℃

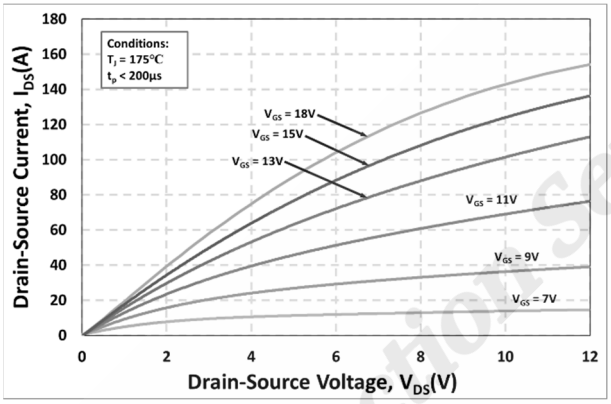


Figure 3. Output Characteristics T_J = 175℃

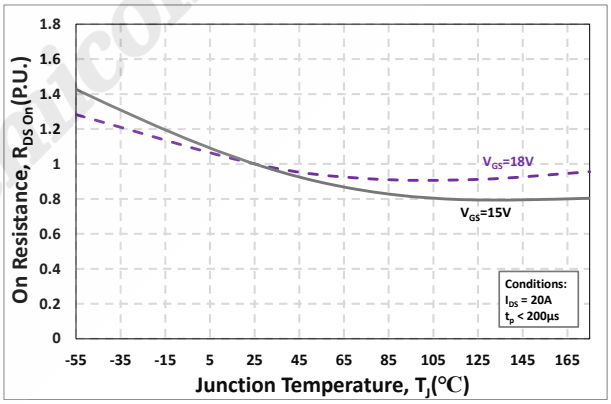


Figure 4. Normalized On-Resistance vs. Temperature

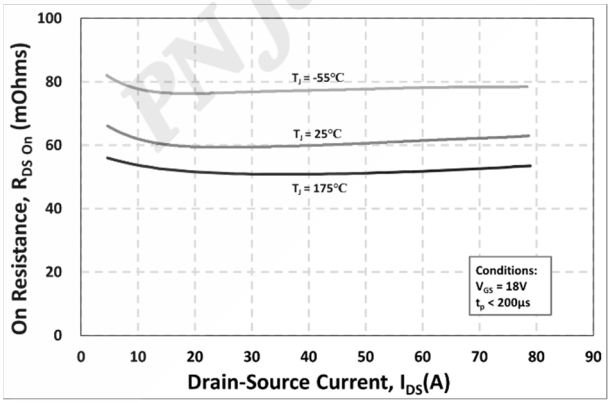


Figure 5. On-Resistance vs. Drain Current Various Temperatures

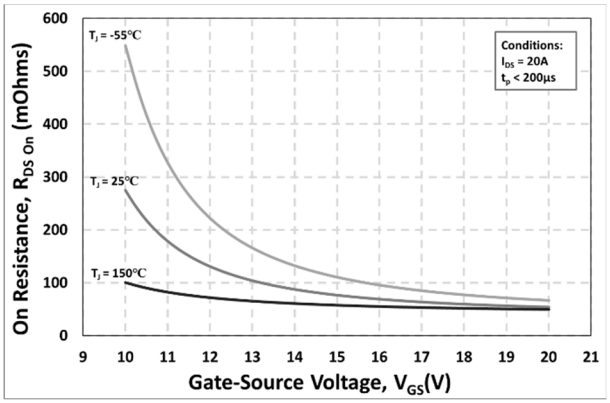


Figure 6. On-Resistance vs. Gate-Source Voltage

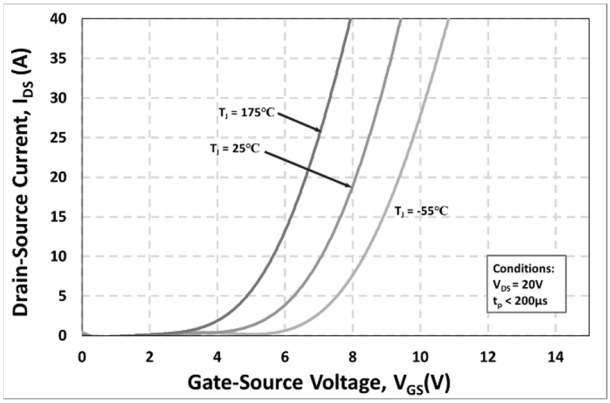


Figure 7. Transfer Characteristic for Various Junction Temperatures

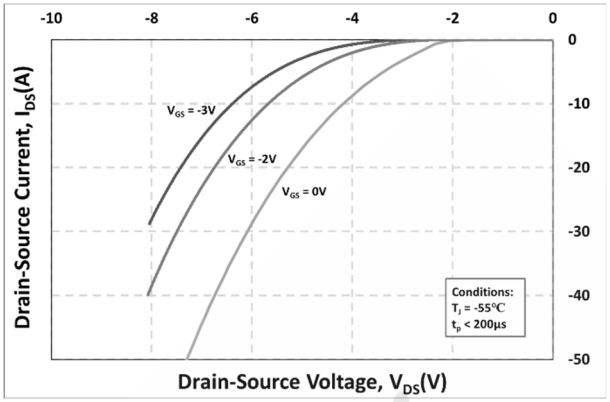


Figure 8. Body Diode Characteristic at -55°C

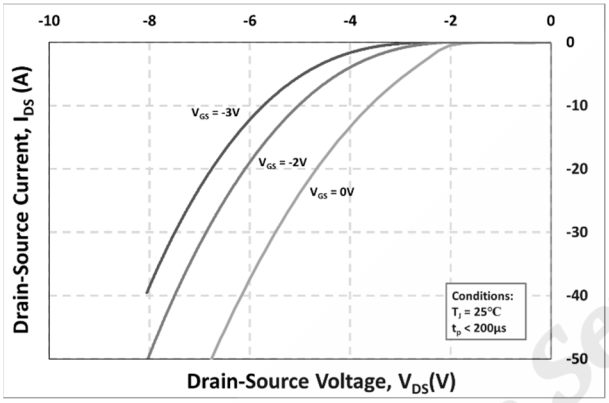


Figure 9. Body Diode Characteristic at 25°C

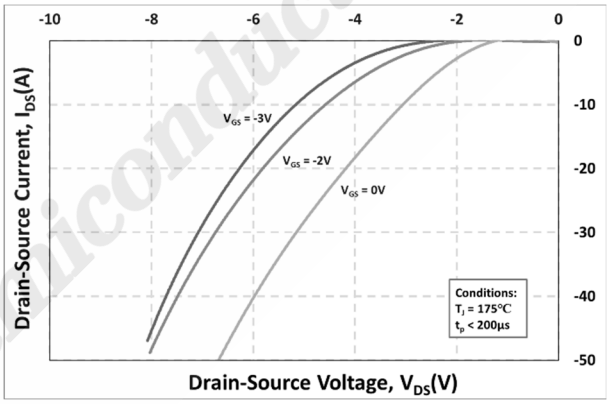


Figure 10. Body Diode Characteristic at 175°C

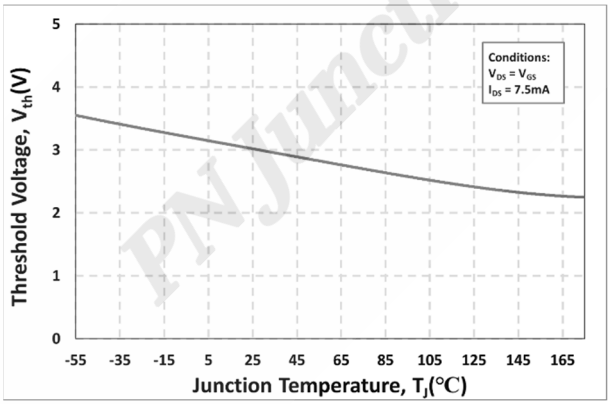


Figure 11. Threshold Voltage vs. Temperature

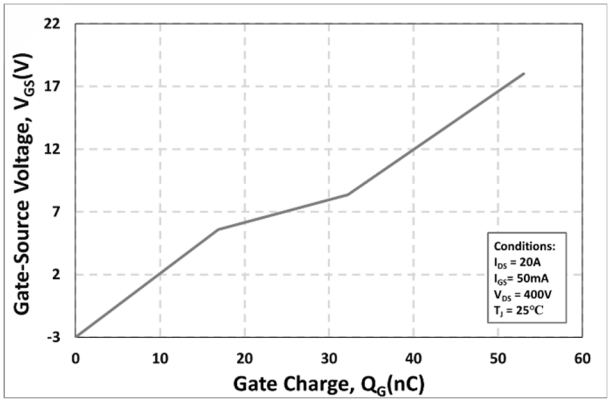


Figure 12. Gate Charge Characteristics

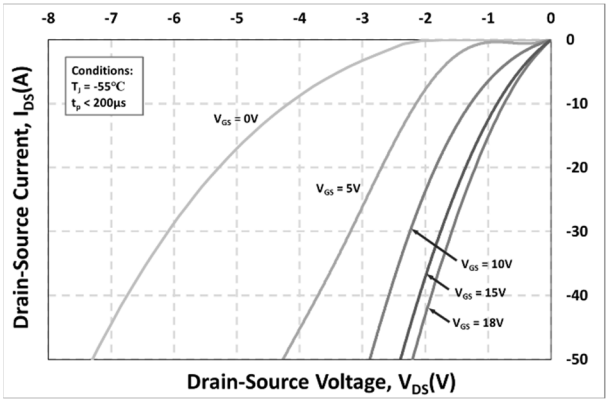


Figure 13. 3rd Quadrant Characteristic at -55°C

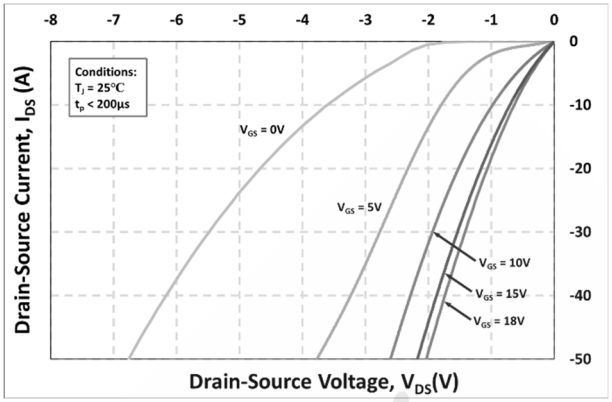


Figure 14. 3rd Quadrant Characteristic at 25°C

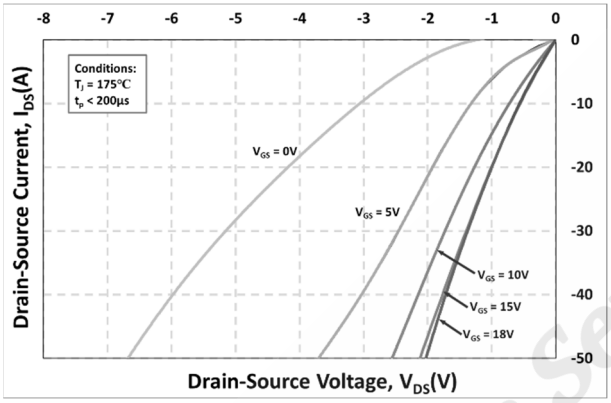


Figure 15. 3rd Quadrant Characteristic at 175°C

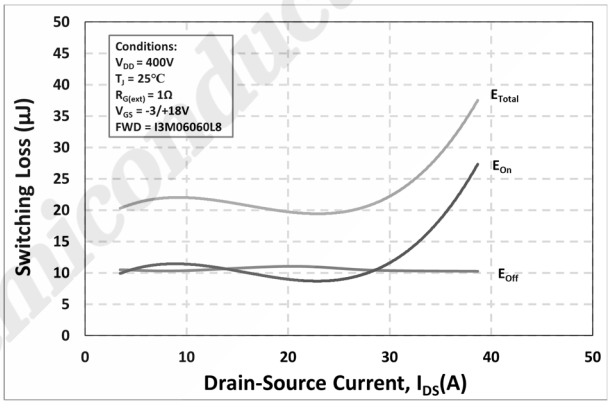


Figure 16. Clamped Inductive Switching Energy vs. Drain Current (VDD=400V)

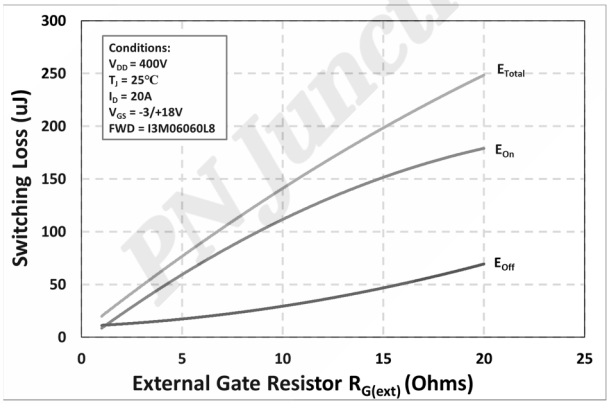


Figure 17. Clamped Inductive Switching Energy vs. $R_{G(ext)}$

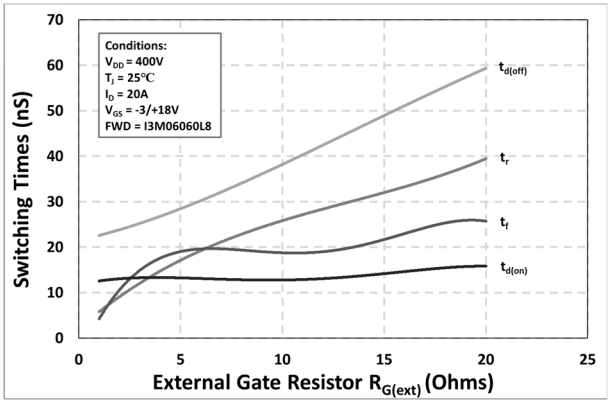


Figure 18. Switching Times vs. $R_{G(ext)}$

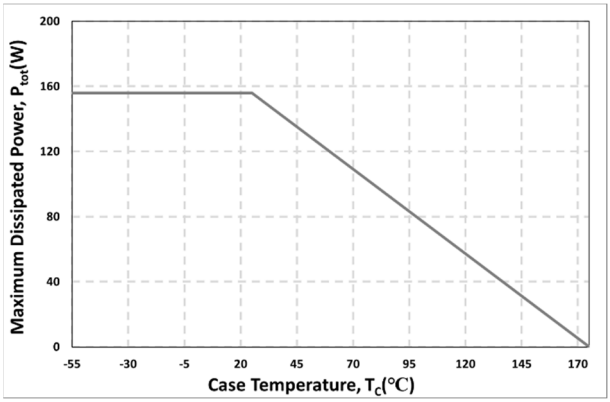


Figure 19. Maximum Power Dissipation Derating vs. Case Temperature

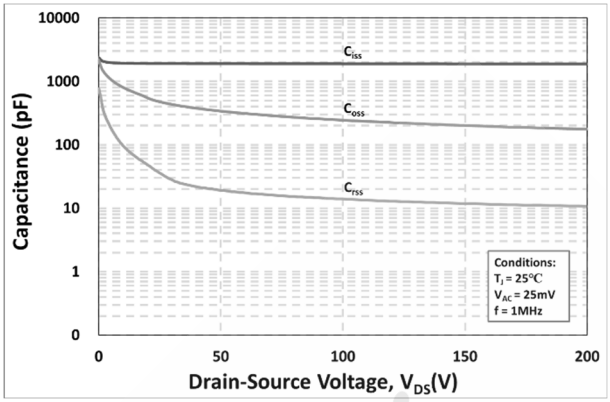


Figure 20. Capacitances vs. Drain-Source Voltage (0 - 200V)

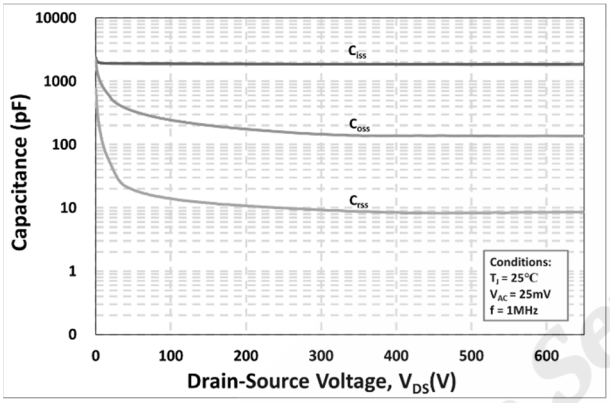


Figure 21. Capacitances vs. Drain-Source Voltage (0 - 650V)

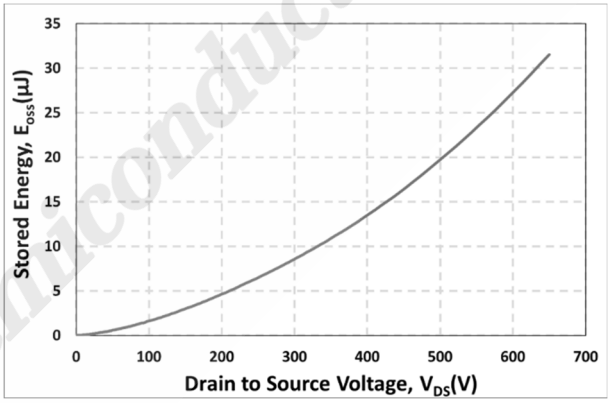


Figure 22. Output Capacitor Stored Energy

6. Definitions

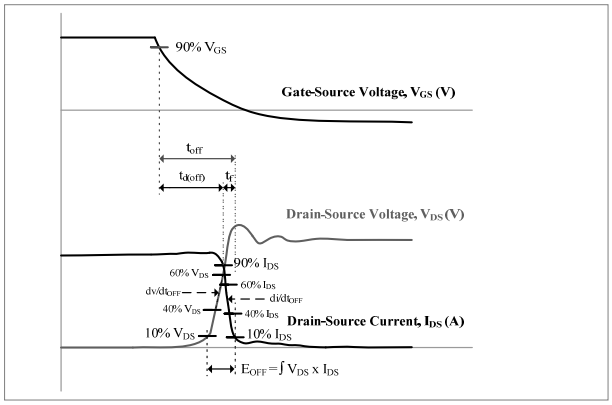


Figure 23. Turn-off Transient Definitions

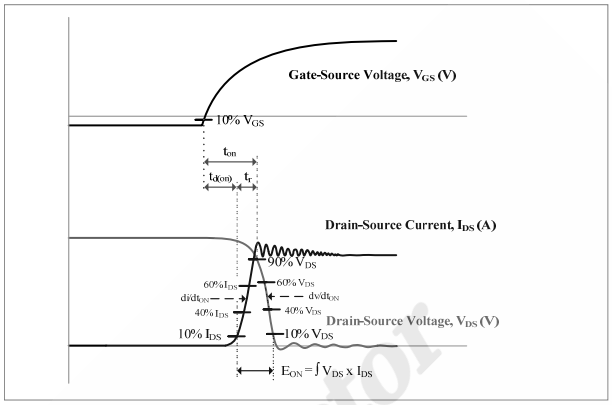


Figure 24. Turn-on Transient Definitions

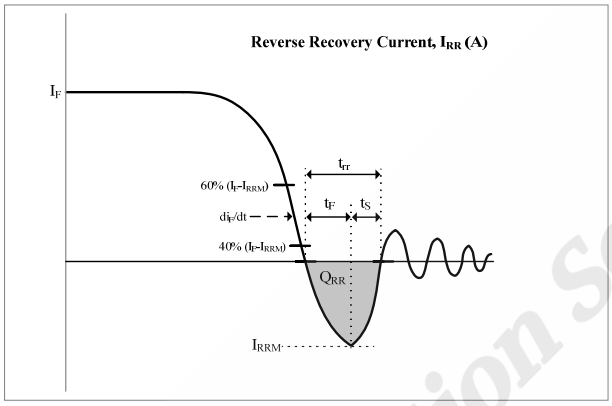


Figure 25. Reverse Recovery Definitions

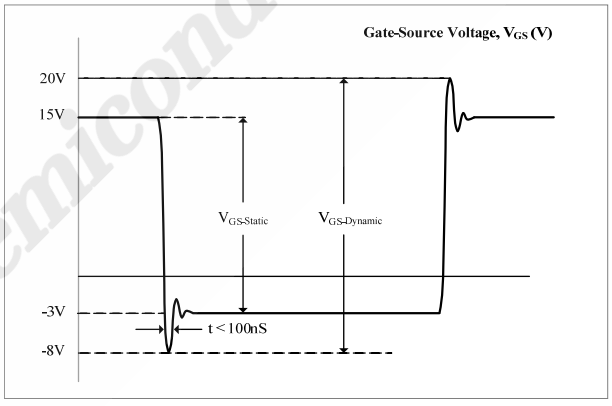
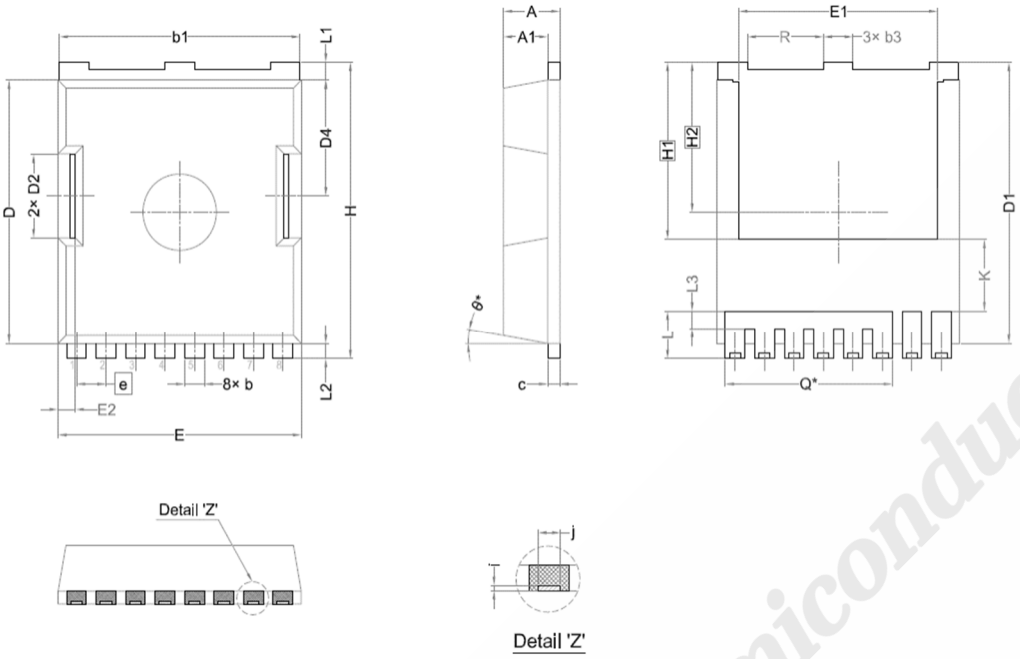


Figure 26. Vgs Transient Definitions

7. Package Outlines



SYMBOL	DIMENSIONS		
	MIN.	NOM.	MAX.
A	2.20	2.30	2.40
A1	1.70	1.80	1.90
b	0.70	0.80	0.90
b1	9.70	9.80	9.90
b3	1.10	1.20	1.30
c	0.40	0.50	0.60
D	10.28	10.38	10.48
D1	10.98	11.08	11.18
D2	3.20	3.30	3.40
D4	4.45	4.55	4.65
E	9.80	9.90	10.00
E1	8.00	8.10	8.20
E2	0.60	0.70	0.80
e	1.20 BSC		
H	11.58	11.68	11.78
H1	6.95 BSC		
H2	5.89 BSC		
i	0.10 REF.		
j	0.46 REF.		
K	2.80 REF.		
L	1.40	1.90	2.10
L1	0.60	0.70	0.80
L2	0.50	0.60	0.70
L3	0.30	0.70	0.80
N	8		
Q	6.80 REF.		
R	3.00	3.10	3.20
θ	10° REF.		

Drawing and Dimensions

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